# **Octal Bus Transceiver**

The MC74VHCT245A is an advanced high speed CMOS octal bus transceiver fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the DIR input. The output enable pin  $(\overline{OE})$  can be used to disable the device, so that the buses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT245A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage-input/output voltage mismatch, battery backup, hot insertion, etc.

### Features

- High Speed:  $t_{PD} = 4.9$  ns (Typ) at  $V_{CC} = 5.0$  V
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 V$ ;  $V_{IH} = 2.0 V$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 1.6 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 304 FETs or 76 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

## **APPLICATION NOTES**

- Do not force a signal on an I/O pin when it is an active output, damage may occur.
- All floating (high impedance) input or I/O pins must be fixed by means of pullup or pulldown resistors or bus terminator ICs.



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.



Figure 1. Logic Diagram

#### **FUNCTION TABLE**

Control	Inputs	
ŌĒ	DIR	Operation
L L H	L H X	Data Tx from Bus B to Bus A Data Tx from Bus A to Bus B Buses Isolated (High–Z State)

DIR [	1●	20	l v <sub>cc</sub>
A1 [	2	19	
A2 [	3	18	] в1
A3 [	4	17	р в2
A4 [	5	16	🛛 вз
A5 [	6	15	р в4
A6 [	7	14	] В5
A7 [	8	13	В6
A8 [	9	12	🛛 в7
	10	11	🛛 в8
			•

#### Figure 2. Pin Assignment

#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		– 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		– 0.5 to + 7.0	V
V <sub>I/O</sub>	DC Output Voltage	Outputs in 3–State High or Low State	- 0.5 to + 7.0 $-$ 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current		- 20	mA
I <sub>OK</sub>	Output Diode Current (V <sub>OUT</sub> < GN	D; V <sub>OUT</sub> > V <sub>CC</sub> )	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, $V_{CC}$ and GND	Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		– 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{\text{in}}$  and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>. Unused inputs must always be

tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected. †Derating -

SOIC Packages: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol		Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		4.5	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>I/O</sub>	DC Output Voltage	Outputs in 3–State High or Low State	0 0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature		- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> =5.0V ±0.5V	0	20	ns/V

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>cc</sub>	Г	[ <sub>A</sub> = 25°	С	$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V <sub>OH</sub>	Minimum High-Level Output	I <sub>OH</sub> = - 50μA	4.5	4.4	4.5		4.4		V
	Voltage V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = - 8mA	4.5	3.94			3.80		
V <sub>OL</sub>	Maximum Low-Level Output	I <sub>OL</sub> = 50μA	4.5		0.0	0.1		0.1	V
	Voltage V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 8mA	4.5			0.36		0.44	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			± 0.1		±1.0	μΑ
I <sub>OZ</sub>	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	5.5			± 0.25		± 2.5	μΑ
ICC	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			4.0		40.0	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	Per Input: V <sub>IN</sub> = 3.4V Other Input: V <sub>CC</sub> or GND	5.5			1.35		1.50	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5V	0			0.5		5.0	μΑ

#### AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

				T <sub>A</sub> = 25°C		T <sub>A</sub> = − 40 to 85°C		$\begin{bmatrix} 1 \\ -1 \end{bmatrix}$	
Symbol	Parameter	Test Cond	litions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay A to B or B to A	$V_{CC}=5.0\pm0.5V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		4.9 5.4	7.7 8.7	1.0 1.0	8.5 9.5	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OE to A or B	$V_{CC} = 5.0 \pm 0.5 V$ $R_L = 1 k \Omega$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		9.4 9.9	13.8 14.8	1.0 1.0	15.0 16.0	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OE to A or B	$V_{CC} = 5.0 \pm 0.5 V$ $R_L = 1 k \Omega$	C <sub>L</sub> = 50pF		10.1	15.4	1.0	16.5	ns
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 5.0 ± 0.5V (Note 1)	C <sub>L</sub> = 50pF			1.0		1.0	ns
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	pF
C <sub>out</sub>	Maximum 3-State Output Capacitance (Output in High-Impedance State)				13				pF
					Туріса	al @ 25°	C, V <sub>CC</sub> = 5	.0V	

			Typical @ 25°C, $v_{CC} = 5.0v$		
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)		16	pF	
1 Doromo		+ 1			

 Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$  (per bit).  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

## NOISE CHARACTERISTICS (Input $t_{f}$ = $t_{f}$ = 3.0ns, $C_{L}$ = 50pF, $V_{CC}$ = 5.0V)

		T <sub>A</sub> = 25°C		
Symbol	Parameter	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	1.2	1.6	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-1.2	-1.6	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHCT245ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT245ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT245ADTG	TSSOP-20*	75 Units / Rail
MC74VHCT245ADTRG	TSSOP-20*	2500 / Tape & Reel
MC74VHCT245AMELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.



Figure 3. Switching Waveform



Figure 4. Switching Waveform







### **PACKAGE DIMENSIONS**

SOIC-20 WB **DW SUFFIX** CASE 751D-05 ISSUE G

A



- NOTES:
  DIMENSIONS ARE IN MILLIMETERS.
  INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

#### PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 ISSUE C



16X

0.36

NOTES:

1. DIMENSIONING AND TOLERANCING PER

 DIMENSIONING AND FOLERANCING P ANSI YI45M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.

INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE --W-.

DIM      MIN      MAX      MIN      MAX        A      6.40      6.60      0.252      0.260        B      4.30      4.50      0.169      0.177        C       1.20       0.047        D      0.05      0.15      0.002      0.006        F      0.50      0.75      0.020      0.30        G      0.65      BSC      0.026      BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.007      0.012		MILLIN	IETERS	INC	HES	
B      4.30      4.50      0.169      0.177        C       1.20       0.047        D      0.05      0.15      0.002      0.006        F      0.50      0.75      0.020      0.030        G      0.65 BSC      0.026 BSC      0.026 BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	DIM	MIN	MAX	MIN	MAX	
C       1.20       0.047        D      0.05      0.15      0.002      0.006        F      0.50      0.75      0.020      0.030        G      0.65      BSC      0.026      BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.008	Α	6.40	6.60	0.252	0.260	
D      0.05      0.15      0.002      0.066        F      0.50      0.75      0.020      0.030        G      0.65      BSC      0.028      BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	В	4.30	4.50	0.169	0.177	
F      0.50      0.75      0.020      0.030        G      0.65 BSC      0.028 BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	С		1.20		0.047	
G      0.65 BSC      0.026 BSC        H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	D	0.05	0.15	0.002	0.006	
H      0.27      0.37      0.011      0.015        J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	F	0.50	0.75	0.020	0.030	
J      0.09      0.20      0.004      0.008        J1      0.09      0.16      0.004      0.006	G	0.65	BSC	0.026	BSC	
J1 0.09 0.16 0.004 0.006	Н	0.27	0.37	0.011	0.015	
	J	0.09	0.20	0.004	0.008	
K 019 030 0007 0012	J1	0.09	0.16	0.004	0.006	
0.001 0.001 0.0012	K	0.19	0.30	0.007	0.012	
K1 0.19 0.25 0.007 0.010	K1	0.19	0.25	0.007 0.010		
L 6.40 BSC 0.252 BSC	L	6.40	BSC	0.252 BSC		
M 0° 8° 0° 8°	М	0°	8°	0 °	8°	

DIMENSIONS: MILLIMETERS

16X

1.26

#### PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE A** 



b

0.13 (0.005) 🕅

 $\oplus$ 



DETAIL P



Δ

0.10 (0.004)

 $\cap$ 

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. 2. 3 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH
- **OR PROTRUSIONS SHALL NOT EXCEED 0.15** (0.006) PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR 4
- TERMINAL NOWBERS ARE SHOWN FOR REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE 5 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS INC		HES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	) BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.81		0.032

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